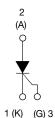
## VS-16TTS08FP-M3, VS-16TTS12FP-M3

Vishay Semiconductors

## **High Voltage Phase Control Thyristor, 16 A**





3L TO-220 FullPAK

PRIMARY CHARACTERISTICS				
I <sub>T(AV)</sub> 10 A				
V <sub>DRM</sub> /V <sub>RRM</sub>	800 V, 1200 V			
$V_{TM}$	1.4 V			
I <sub>GT</sub>	60 mA			
$T_J$	-40 °C to 125 °C			
Package	3L TO-220 FullPAK			
Circuit configuration	Single SCR			

#### **FEATURES**

- · Designed and qualified for industrial level
- Fully isolated package (V<sub>INS</sub> = 2500 V<sub>RMS</sub>)
- UL pending
- 125 °C max. operating junction temperature
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912



#### **APPLICATIONS**

 Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery charge

#### **DESCRIPTION**

The VS-16TTS..FP... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS						
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS			
Capacitive input filter $T_A = 55$ °C, $T_J = 125$ °C, common heatsink of 1 °C/W	13.5	17	А			

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
I <sub>T(AV)</sub>	Sinusoidal waveform	10	۸		
I <sub>RMS</sub>		16	Α		
V <sub>DRM</sub> /V <sub>RRM</sub>		800, 1200	V		
I <sub>TSM</sub>		200	A		
V <sub>T</sub>	10 A, T <sub>J</sub> = 25 °C	1.4	V		
dV/dt		500	V/µs		
dl/dt		150	A/µs		
TJ	Range	-40 to 125	°C		

VOLTAGE RATINGS			
PART NUMBER	V <sub>RRM</sub> , MAXIMUM PEAK REVERSE VOLTAGE V	V <sub>DRM</sub> , MAXIMUM PEAK DIRECT VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> AT 125 °C mA
VS-16TTS08FP-M3	800	800	10
VS-16TTS12FP-M3	1200	1200	10



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ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEGT COMPLETIONS		VALUES		UNITS	
PANAMETEN			TEST CONDITIONS	TYP.	MAX.	UNITS	
Maximum average on-state current	I <sub>T(AV)</sub>	T <sub>C</sub> = 70 °C,	180° conduction, half sine wave	1	0		
Maximum RMS on-state current	I <sub>RMS</sub>			1	6	Α	
Maximum peak, one-cycle,	ı	10 ms sine p	oulse, rated V <sub>RRM</sub> applied	1	70	A .	
non-repetitive surge current	I <sub>TSM</sub>	10 ms sine p	ulse, no voltage reapplied	2	00		
Maximum I <sup>2</sup> t for fusing	l <sup>2</sup> t	10 ms sine p	oulse, rated V <sub>RRM</sub> applied	1-	44	A <sup>2</sup> s	
Maximum i-t for fusing	1-1	10 ms sine p	10 ms sine pulse, no voltage reapplied		00	A-S	
Maximum I $^2\sqrt{t}$ for fusing	I <sup>2</sup> √t	t = 0.1 to 10	t = 0.1 to 10 ms, no voltage reapplied		00	A²√s	
Maximum on-state voltage drop	$V_{TM}$	10 A, T <sub>J</sub> = 25	10 A, T <sub>J</sub> = 25 °C		.4	V	
On-state slope resistance	r <sub>t</sub>	T <sub>.1</sub> = 125 °C		24	1.0	mΩ	
Threshold voltage	V <sub>T(TO)</sub>	1j=125 C	I <sub>J</sub> = 125 °C		.1	V	
Maximum reverse and direct lockage current	1 /1	T <sub>J</sub> = 25 °C	V Peter V A	0	.5		
Maximum reverse and direct leakage current	I <sub>RM</sub> /I <sub>DM</sub>	$V_R = Rated V_{RRM}/V_{DRM}$		$T_J = 125  ^{\circ}\text{C}$ $V_R = \text{Rated } V_{RRM}$	1	0	
Holding current	I <sub>H</sub>		$y = 6 \text{ V}$ , resistive load, initial $I_T = 1 \text{ A}$ 16TTS12FP, $T_J = 25 \text{ °C}$	-	150	mA	
Maximum latching current	IL	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C		2	00		
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J \text{ max., linear to } 80 \text{ %, } V_{DRM} = R_g - k = Open$		5	00	V/µs	
Maximum rate of rise of turned-on current	dl/dt			1:	50	A/µs	

TRIGGERING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	$P_{GM}$		8.0	w
Maximum average gate power	P <sub>G(AV)</sub>		2.0	]
Maximum peak positive gate current	+ I <sub>GM</sub>		1.5	Α
Maximum peak negative gate voltage	- V <sub>GM</sub>		10	٧
	I <sub>GT</sub>	Anode supply = 6 V, resistive load, T <sub>J</sub> = -10 °C	90	mA
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	60	
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	35	
		Anode supply = 6 V, resistive load, T <sub>J</sub> = -10 °C	3.0	
Maximum required DC gate voltage to trigger	V <sub>GT</sub>	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	2.0	v
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	1.0	]
Maximum DC gate voltage not to trigger	$V_{GD}$	T. = 125 °C V Patod value	0.25	
Maximum DC gate current not to trigger	$I_{GD}$	$T_J = 125$ °C, $V_{DRM} = Rated value$ 2.		mA

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t <sub>gt</sub>	T <sub>J</sub> = 25 °C	0.9	
Typical reverse recovery time	t <sub>rr</sub>	T <sub>.I</sub> = 125 °C	4	μs
Typical turn-off time	tq	1 1 1 1 2 3 0	110	1



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THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range		T <sub>J</sub> , T <sub>Stg</sub>		-40 to +125	°C
Maximum thermal resistance, junction to case		$R_{thJC}$	DC operation	2.5	
Maximum thermal resistance, junction to ambient		R <sub>thJA</sub>		62	°C/W
Typical thermal resistance, case to heatsink		$R_{\text{thCS}}$	Mounting surface, smooth, and greased	0.5	
Approximate weight				2	g
Approximate weight				0.07	OZ.
Mounting torque	minimum			6 (5)	kgf ⋅ cm
	maximum			12 (10)	(lbf · in)
				16TTS	08FP
Marking device		Case style 3L TO-220 FullPAK	16TTS	12FP	

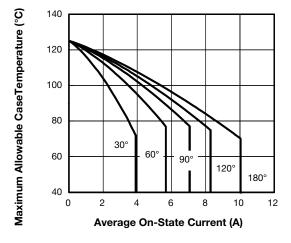


Fig. 1 - Current Rating Characteristics

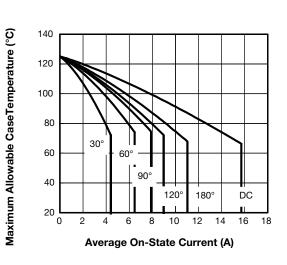


Fig. 2 - Current Rating Characteristics

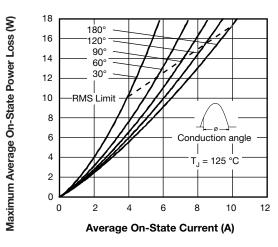


Fig. 3 - On-State Power Loss Characteristics

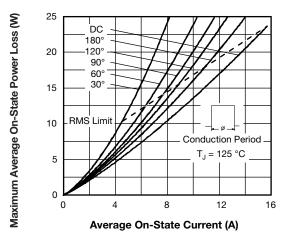
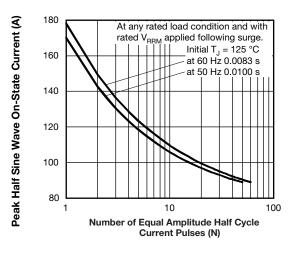


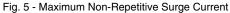
Fig. 4 - On-State Power Loss Characteristics



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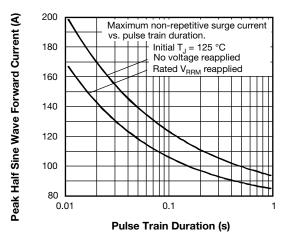


Fig. 6 - Maximum Non-Repetitive Surge Current

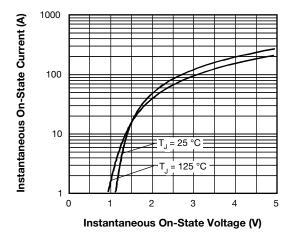


Fig. 7 - On-State Voltage Drop Characteristics

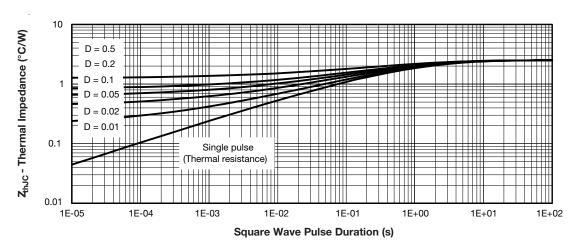


Fig. 8 - Thermal Impedance Z<sub>thJC</sub> Characteristics

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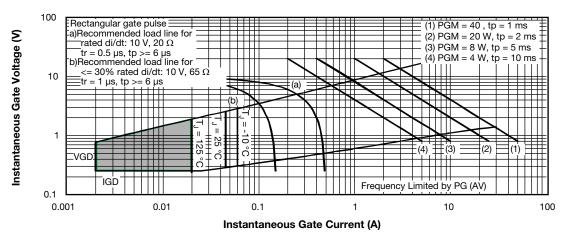
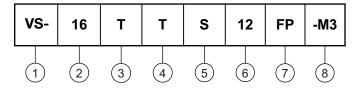


Fig. 9 - Gate Characteristics

### ORDERING INFORMATION TABLE

### Device code



1 - Vishay Semiconductors product

Current rating, RMS value

**3** - Circuit configuration:

T = single thyristor

4 - Package:

T = TO-220AB

5 - Type of silicon:

S = converter grade

6 - Voltage code x 100 = V<sub>RRM</sub> - 08 = 800 V 12 = 1200 V

7 - FullPAK

8 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-16TTS08FP-M3	50	1000	Antistatic plastic tubes			
VS-16TTS12FP-M3	50	1000	Antistatic plastic tubes			

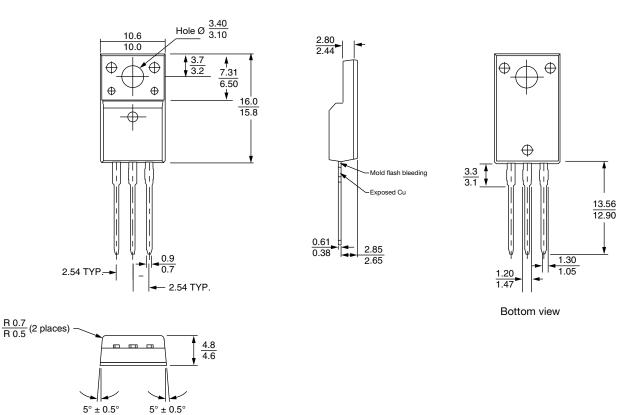
LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?96155</u>					
Part marking information	www.vishay.com/doc?95456				



Vishay Semiconductors

### **3L TO-220 FullPAK**

#### **DIMENSIONS** in millimeters



#### **Notes**

- (1) All dimensions are in mm
- (2) Package body size exclude mold flash and burrs. Moldflash should be less than 6 mils



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